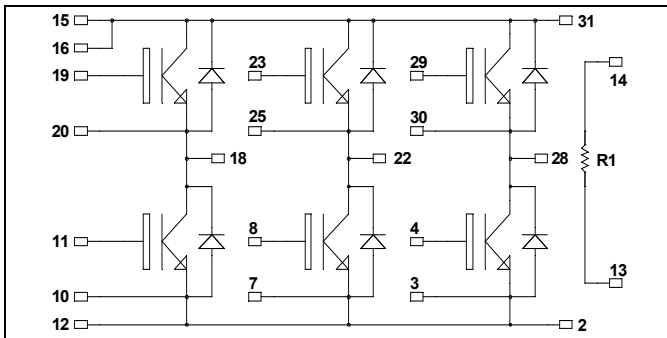
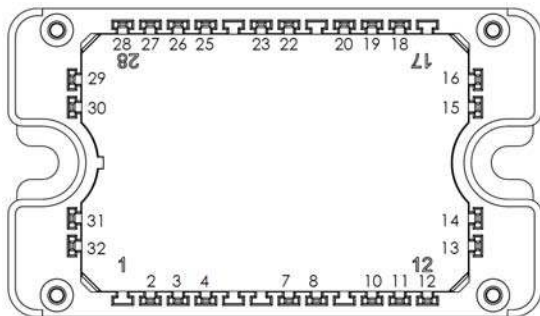


**3 Phase bridge  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 1200V$   
 $I_C = 35A @ T_c = 80^\circ C$**



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.



### Application

- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

**All ratings @  $T_j = 25^\circ C$  unless otherwise specified**

### Absolute maximum ratings (Per IGBT)

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage	1200	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	55
		$T_c = 80^\circ C$	35
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	70
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Power Dissipation	$T_c = 25^\circ C$	208
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	70A@1150V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

**Electrical Characteristics (Per IGBT)**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ ; $V_{CE} = 1200V$			250	$\mu A$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 35A$		1.7 2.0	2.1	V
		$T_j = 25^\circ C$ $T_j = 125^\circ C$				
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1.5mA$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V$ , $V_{CE} = 0V$			400	nA

**Dynamic Characteristics (Per IGBT)**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$ , $V_{CE} = 25V$		2.5		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		0.15		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ C$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 35A$ $R_G = 27\Omega$		90		ns
$T_r$	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			420		
$T_f$	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ C$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 35A$ $R_G = 27\Omega$		90		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			520		
$T_f$	Fall Time			90		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$		3.5		mJ
		$T_j = 125^\circ C$				
$E_{off}$	Turn-off Switching Energy	$I_C = 35A$ $R_G = 27\Omega$		4.1		
		$T_j = 125^\circ C$				
$R_{thJC}$	Junction to Case Thermal Resistance				0.6	$^\circ C/W$

**Reverse diode ratings and characteristics (Per diode)**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage				1200	V
$I_{RM}$	Reverse Leakage Current	$V_R = 1200V$			100	$\mu A$
$I_F$	DC Forward Current	$T_c = 80^\circ C$		30		A
$V_F$	Diode Forward Voltage	$I_F = 30A$		2.6	3.1	V
		$I_F = 60A$		3.2		
		$I_F = 30A$	$T_j = 125^\circ C$		1.8	
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$		300	ns
			$T_j = 125^\circ C$		380	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$		360	nC
			$T_j = 125^\circ C$		1700	
$R_{thJC}$	Junction to Case Thermal Resistance				1.2	$^\circ C/W$

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

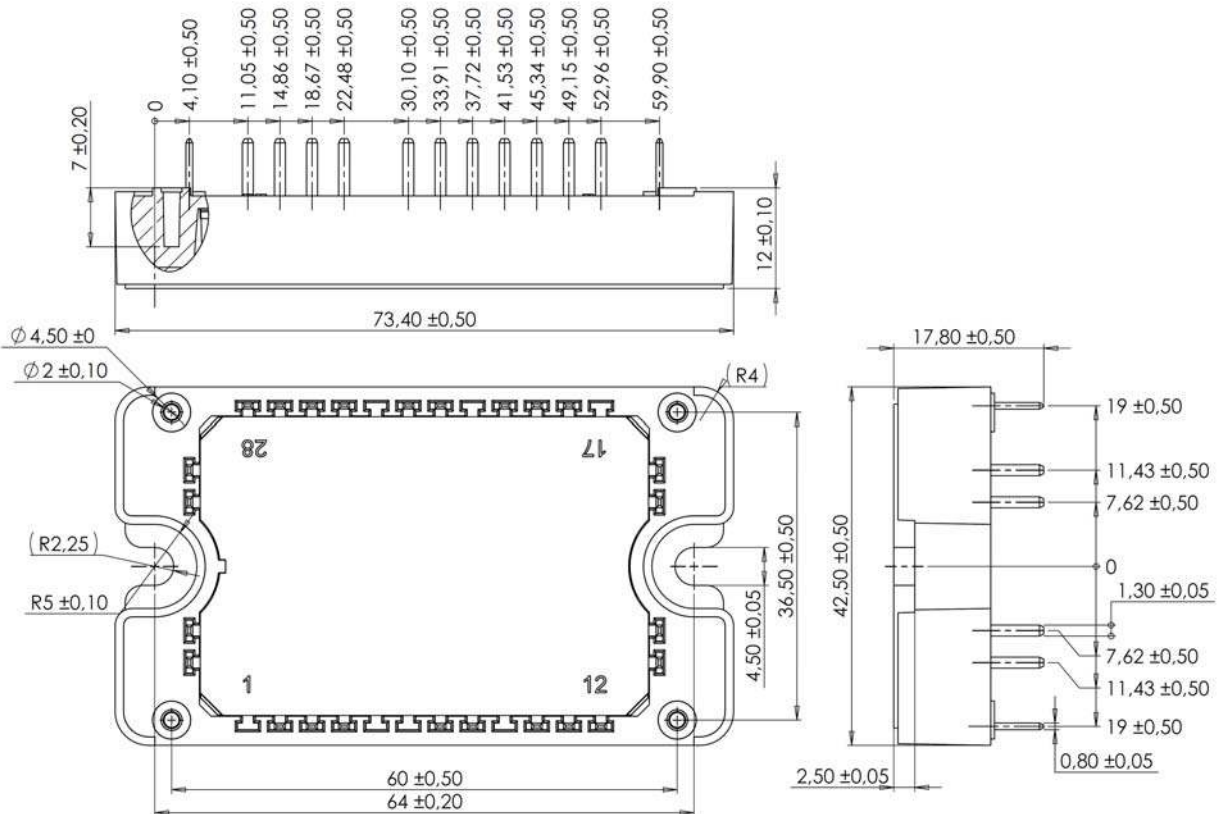
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

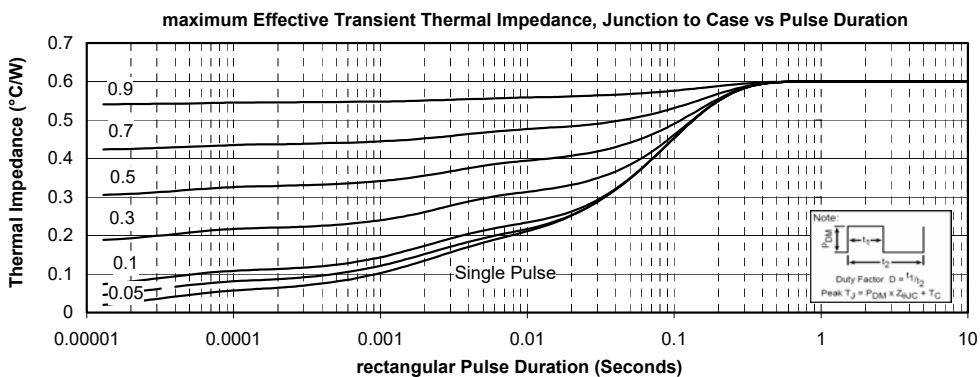
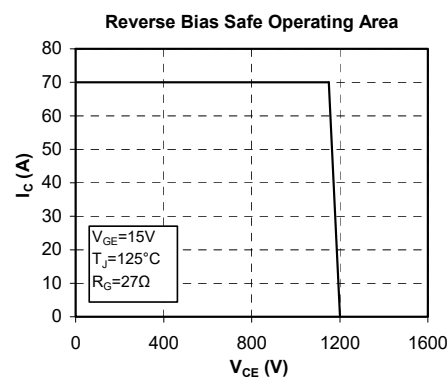
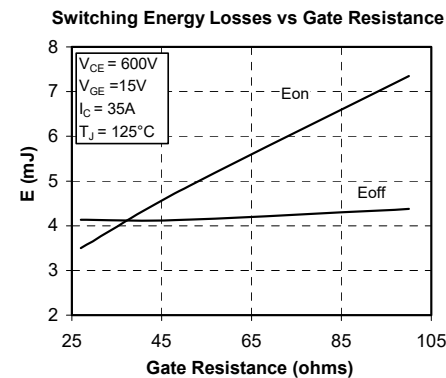
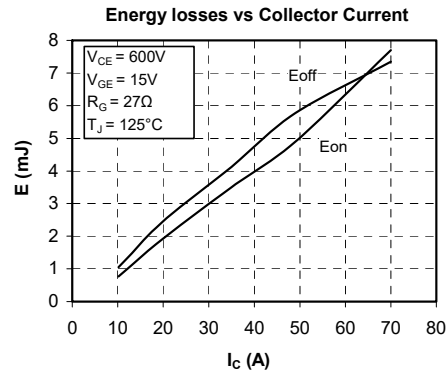
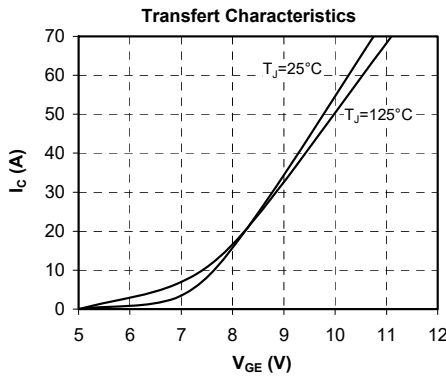
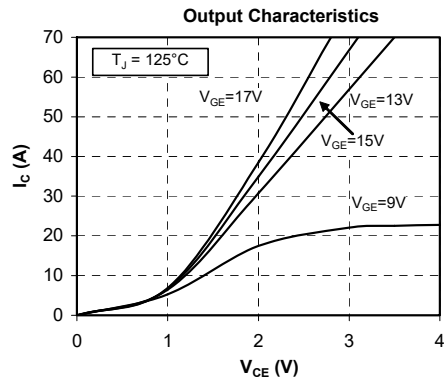
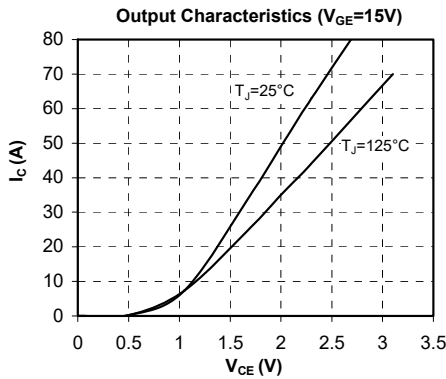
Symbol	Characteristic	Min	Max	Unit		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V		
T <sub>J</sub>	Operating junction temperature range	-40	150	°C		
T <sub>JOP</sub>	Recommended junction temperature under switching conditions	-40	T <sub>Jmax</sub> - 25			
T <sub>STG</sub>	Storage Temperature Range	-40	125			
T <sub>C</sub>	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

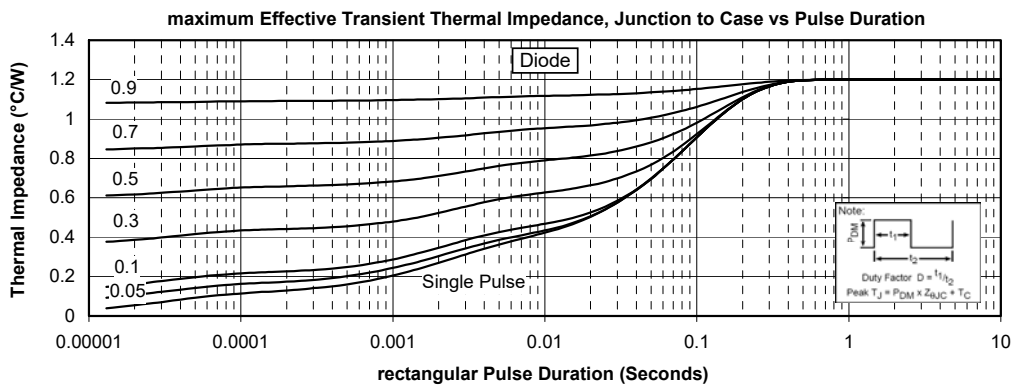
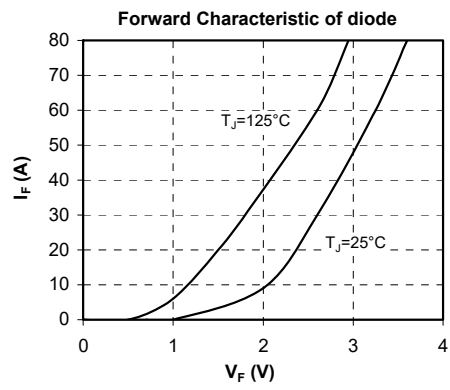
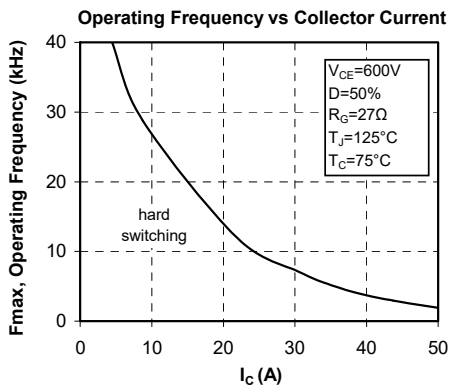
### Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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